SOT23-3 P MOS

P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

V_{DS} (V) = -12V I_D = -8.0A

$R_{DS(ON)}$@-10V≤20mΩ(Type.18mΩ)

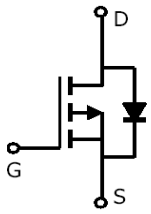
$R_{DS(ON)}$@-4.5V≤25mΩ(Type.21mΩ)

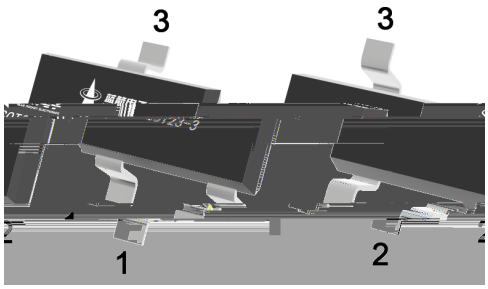
$R_{DS(ON)}$@-2.5V≤30mΩ(Type.27mΩ)

$R_{DS(ON)}$@-1.8V≤50mΩ(Type.40mΩ)

HF Product.

PWM applications,Load switch,Power management.





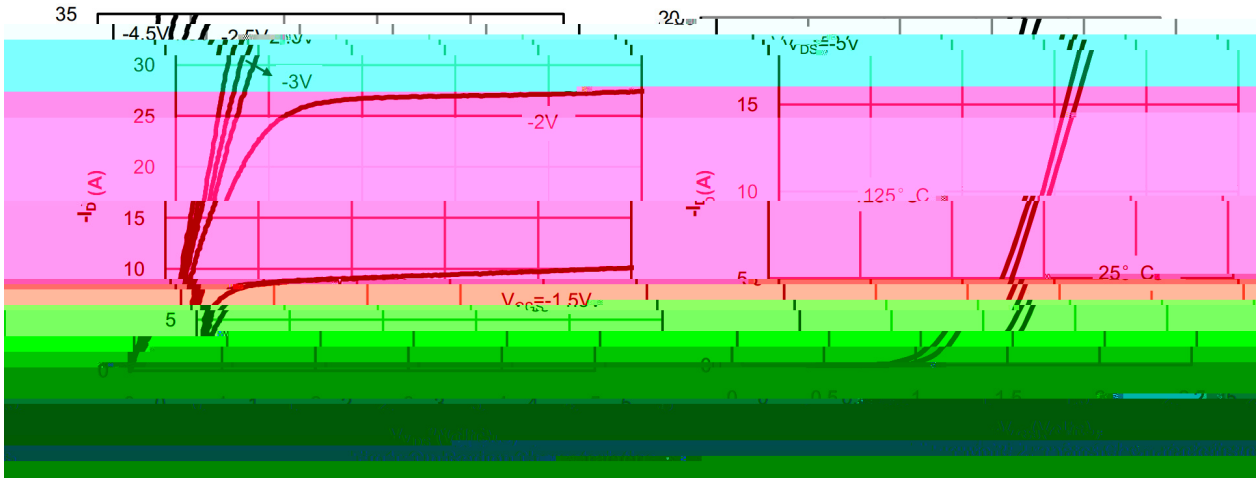
PIN1 G PIN 2 S PIN 3 D

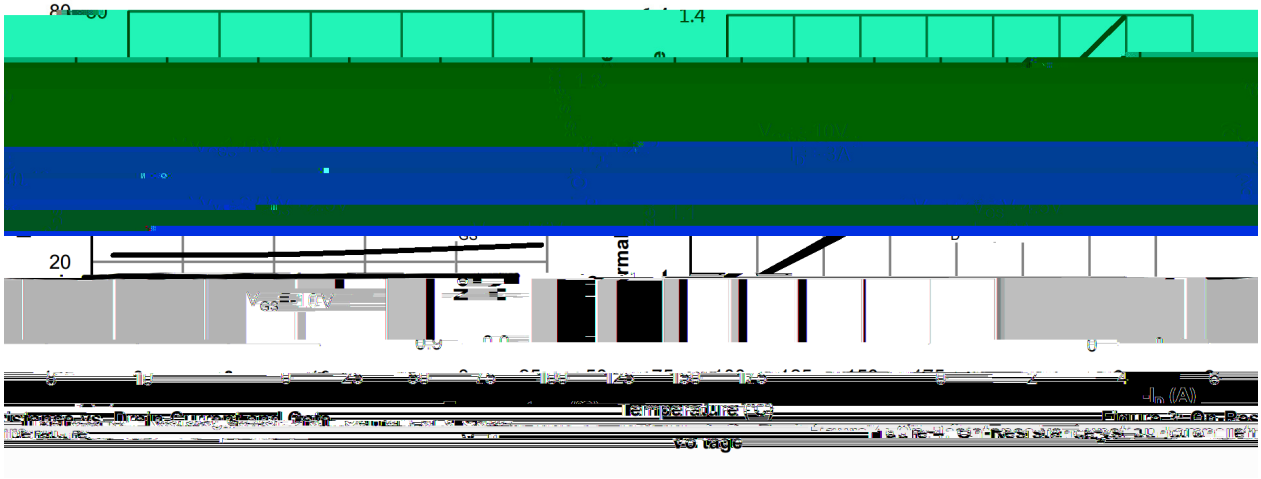
See Marking Instructions.

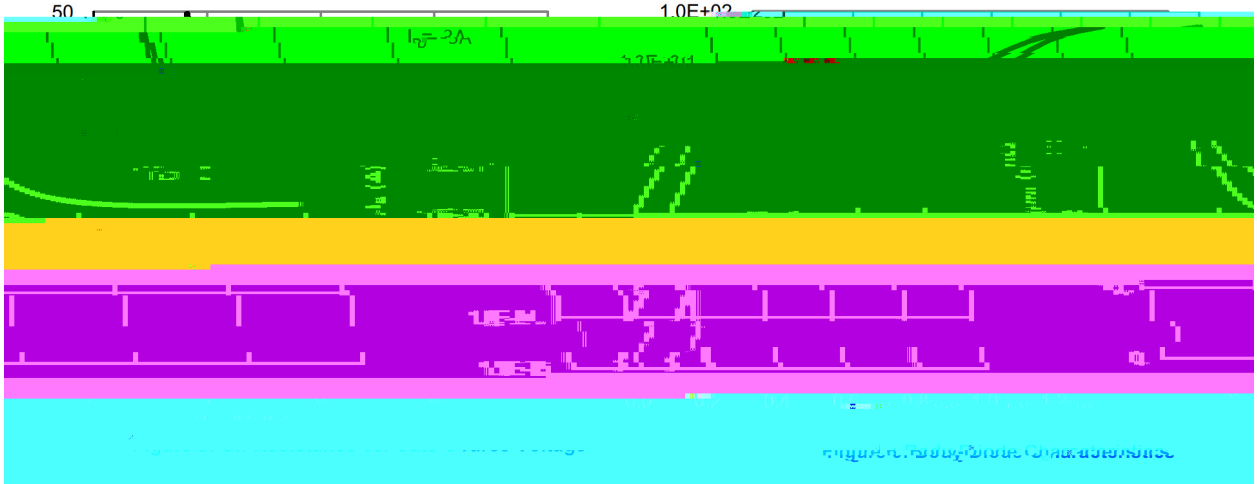
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-12	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current	I_D(T_C=25)	-8.0	A
Pulsed Drain Current	I_{DM}	-25	A
Power Dissipation for Single Operation	P_D(T_C=25)	1.8	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance-Junction to Amibient	$R_{\theta JA}$	125	/W
Thermal Resistance-Junction to Case	$R_{\theta JC}$	69	/W

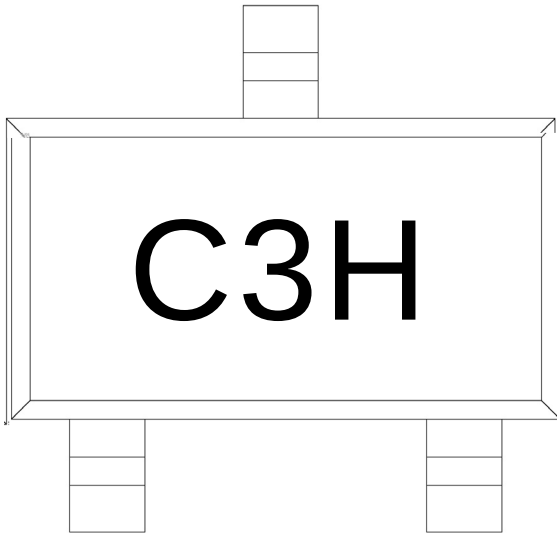
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA V_{GS}=0V	-12	-17.5		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-12V V_{GS}=0V			-1.0	μA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V V_{GS}=±8V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS I_D=-250μA	-0.5	-0.6	-1.0	V

Rev.A Jun.-2023


35
-4.5V
30
-3V
25
-2V
20
15
10
5
-I_D (A)
V_GS=-1.5V
20
V_DS=-5V
15
10
125° C
25° C
-I_S (A)


1.4
20
-I_D (A)


50
1.0E+02



C3

H

Note:

C3: Product Type Code

H: Company Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



				Note:
1	150	180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5		5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3				